



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-363 Plastic-Encapsulate Diode

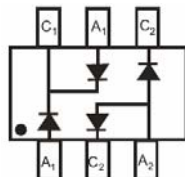
BAV756DW

SWITCHING DIODE

SOT-363

FEATURES

- Fast Switching Speed
- Ultra-Small Surface Mount Package
- For General Purpose Switching Applications
- High Conductance



MAKING: KCA

Maximum Ratings @T_A=25°C

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	75	V
Forward Continuous Current	I _{FM}	300	mA
Average Rectified Output Current	I _O	150	mA
Non-Repetitive Peak Forward Surge Current	I _{FSM}	2	A
@ t = 1.0μs @ t = 1.0s		1	
Power Dissipation	P _D	200	mW
Thermal Resistance Junction to Ambient Air	R _{θJA}	625	°C/W
Operating Junction Temperature	T _J	150	°C
Storage temperature	T _{STG}	-65-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	V _{(BR)R}	I _R = 2.5μA	75		V
Reverse voltage leakage current	I _R	V _R =75V V _R =20V		2.5 0.025	μA
Forward voltage	V _F	I _F =1mA I _F =10mA I _F =50mA I _F =150mA		715 855 1000 1250	mV
Junction capacitance	C _T	V _R =0, f=1MHz		2	pF
Reveres recovery time	t _{rr}	I _F =I _R =10mA, I _{rr} =0.1×I _R , R _L =100Ω		4	nS

Typical Characteristics

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